

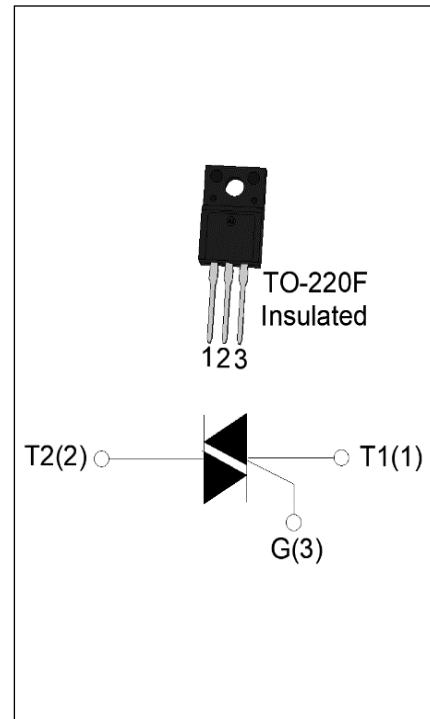


JST08F-800B 8A TRIAC

Rev.A.1.0

DESCRIPTION:

The JST08F-800B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an external plastic package, JST08F-800B provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\text{ I/II/III/IV}}$	50/50/50/70	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leqslant 93^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II III-IV	dI/dt	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}		
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.7)	V _{PP}	1	kV
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ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX.	50	mA
		IV		70	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III - IV	MAX.	50	mA
		II		100	
I _H	I _T =200mA		MAX.	60	mA
dV/dt	V _D =540V Gate Open T _j =125°C		MIN.	1000	V/μs
(dV/dt)c	(dI/dt)c=3.5A/ms, T _j =125°C		MIN.	12	V/μs
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25°C		TYP.	5	μs
t _{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =11A t _p =380μs	T _j =25°C	1.5	V
V _{TO}	Threshold voltage	T _j =125°C	0.81	V
R _D	Dynamic resistance	T _j =125°C	44	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5	μA
I _{RRM}		T _j =125°C	0.35	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	2.8	°C/W
R _{th(j-a)}	junction to ambient (AC)	60	°C/W

ORDERING INFORMATION

J	ST	08	F	-800	B
JieJie Microelectronics Co., Ltd					

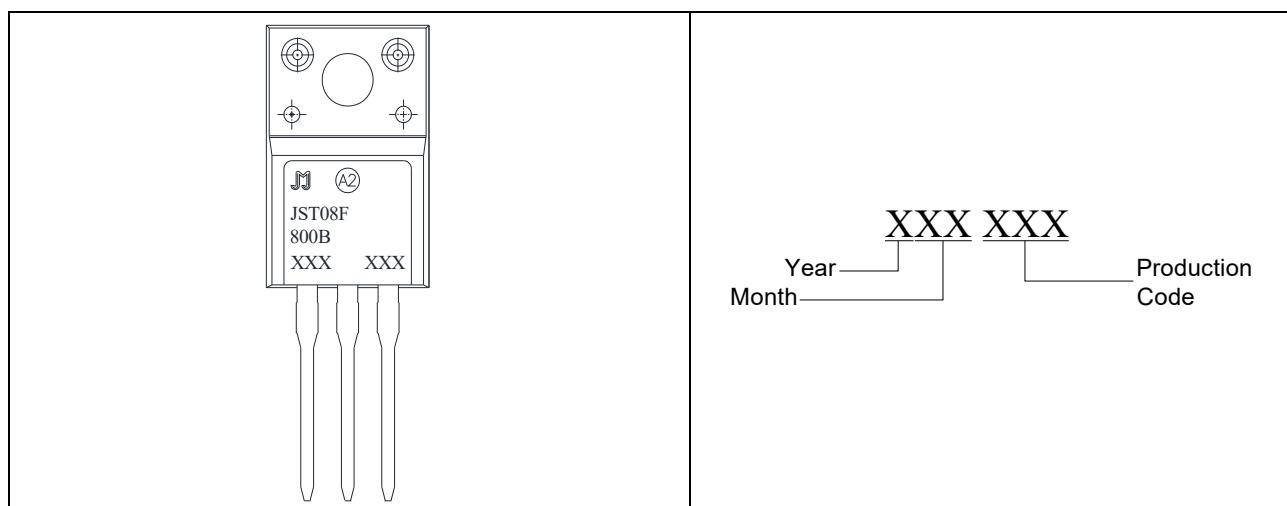
J
JieJie Microelectronics Co., Ltd
TriacsST
I_{T(RMS)}:8A08
F:TO-220F(Ins)F
-800
BB:I_{G1-3}≤50mA I_{G4}≤70mA800:V_{DRM} / V_{RRM}≥800V**MARKING**

FIG.1 Maximum power dissipation versus RMS on-state current

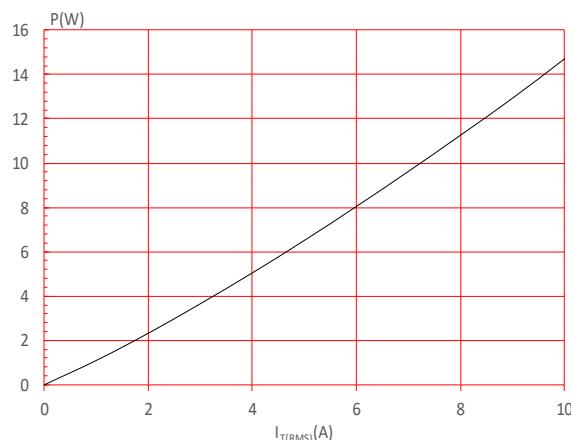


FIG.3: Surge peak on-state current versus number of cycles

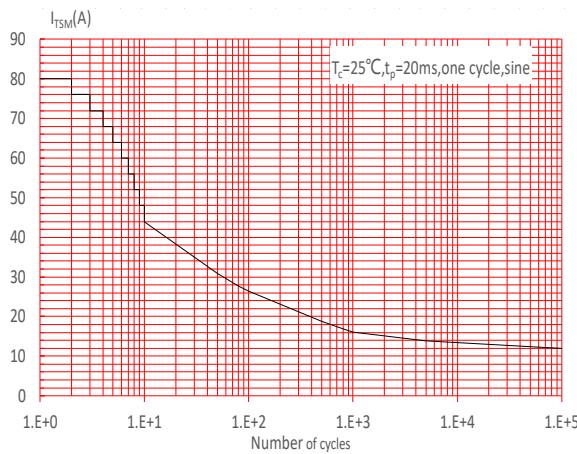


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II : $dI/dt < 100\text{A}/\mu\text{s}$; III-IV: $dI/dt < 50\text{A}/\mu\text{s}$)

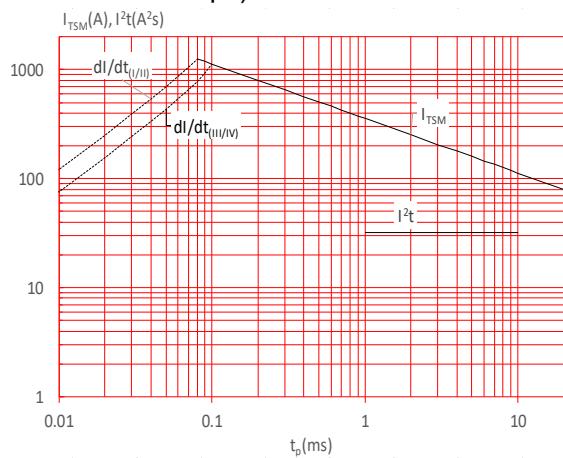


FIG.2: RMS on-state current versus case temperature

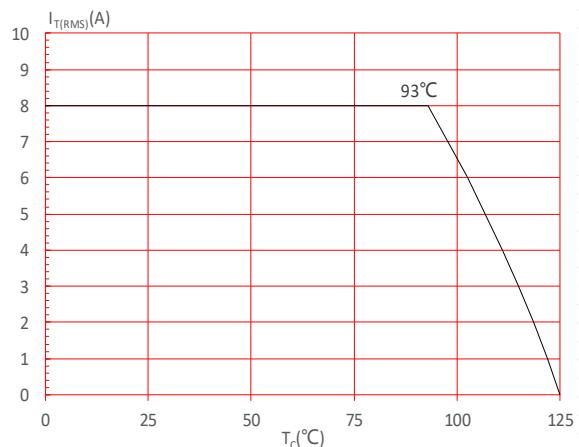


FIG.4: On-state characteristics

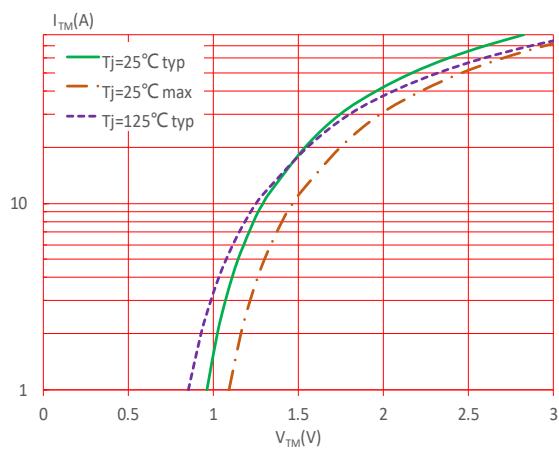


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

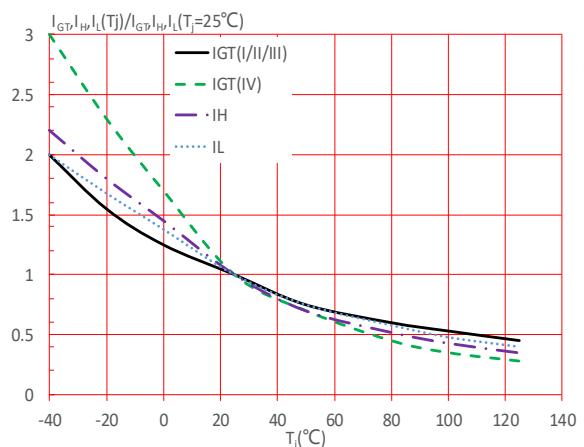
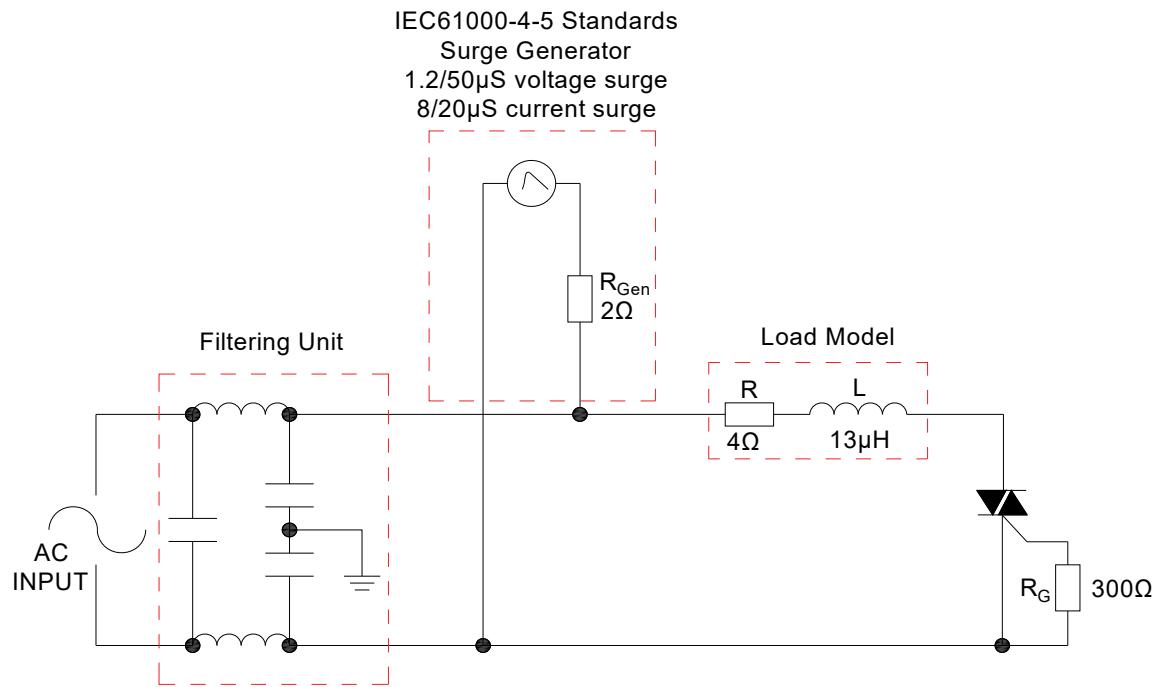


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

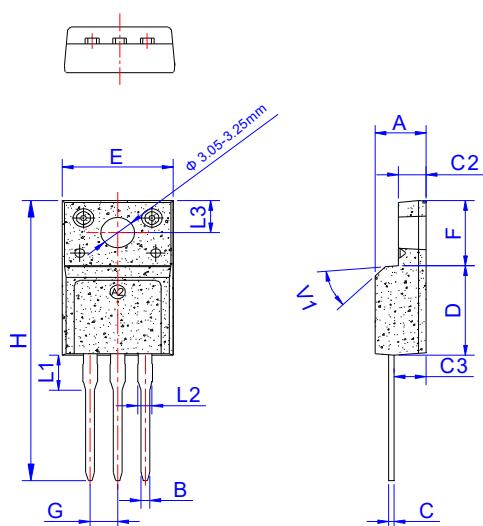
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II -III	IV			
JST08F-800B	800	50	70	TO-220F(Ins)	50	Tube

Document Revision History

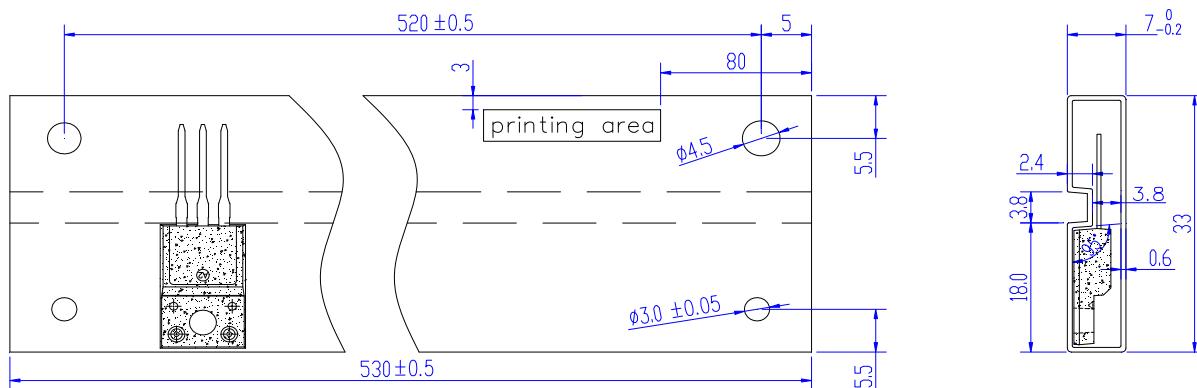
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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